

forming a gate electrode for controlling said MIS transistor which extends above said bypass film and is electrically coupled to said bypass film; and

performing a work process directed to the manufacture of the semiconductor apparatus while performing destaticization through said bypass film.

15. (Original) A method of manufacturing a semiconductor apparatus according to claim 14, further comprising the steps of:

selectively etching a gate insulation film of a region forming said bypass film to make the same thin after said gate insulation film of said MIS transistor has been formed; and

forming said gate electrode to have a pattern extending from a region of said MIS transistor to a portion above said bypass film.

16. (Original) A method of manufacturing a semiconductor apparatus according to claim 14, further comprising the steps of:

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forming a first gate insulation film of said MIS transistor, then selectively etching off said first gate insulation film at a region of said bypass film and forming a second gate insulation film which will become said bypass film; and

then forming said gate electrode to have a pattern extending from a region of said MIS transistor to a portion above said bypass film.

17. (Currently Amended) A method of manufacturing a solid state image device comprising the steps of:

forming a bypass film through which a leak current is able to easily flow as compared with a gate insulation film, between a wiring for connecting each gate electrodes of a MOS transistor forming the pixel and a drain region located other than within any active region, and carrying out a work process while performing destaticization through said bypass film.